

Symbol	Conditions	Characteristic Values		
I_R, I_D	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5	mA
V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.64	V
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85	V	
r_T		11	mΩ	
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	1.5	V
	$T_{VJ} = -40^\circ\text{C}$	\leq	1.6	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	100	mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	200	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	\leq	0.2	V
I_{GD}		\leq	10	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	150	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	100	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	2	μs
R_{thJC}	DC current		0.62	K/W
R_{thJH}	DC current		0.82	K/W
a	Max. acceleration, 50 Hz		50	m/s ²

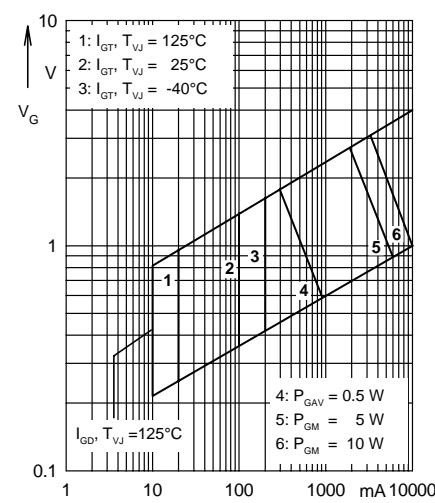
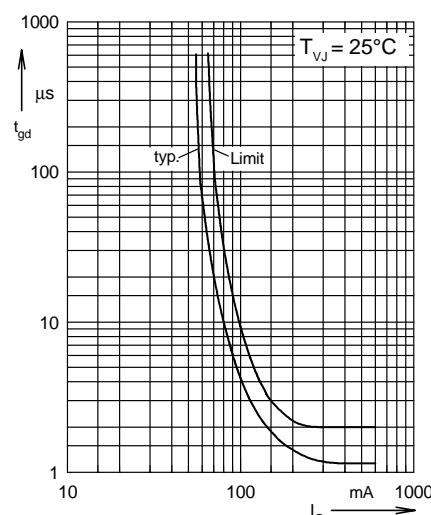
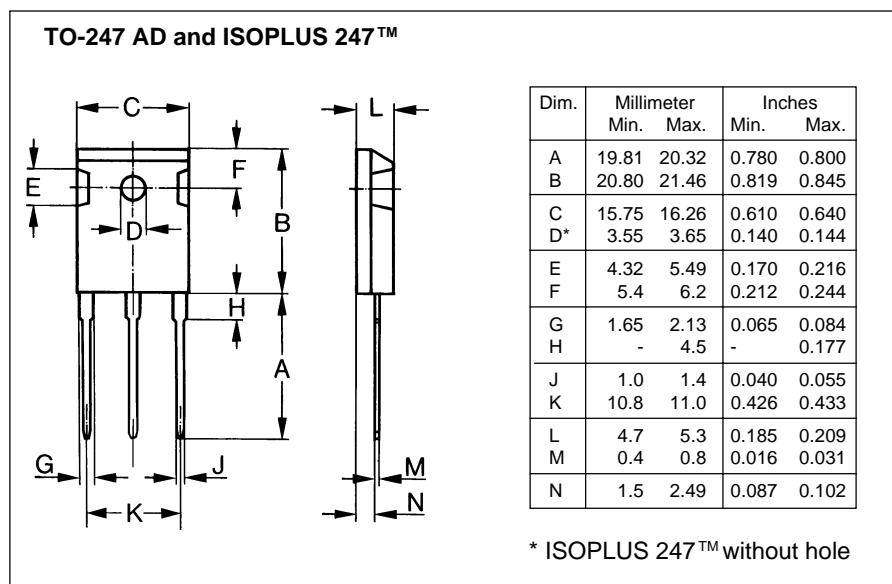


Fig. 1 Gate trigger range

Fig. 2 Gate controlled delay time t_{gd} 

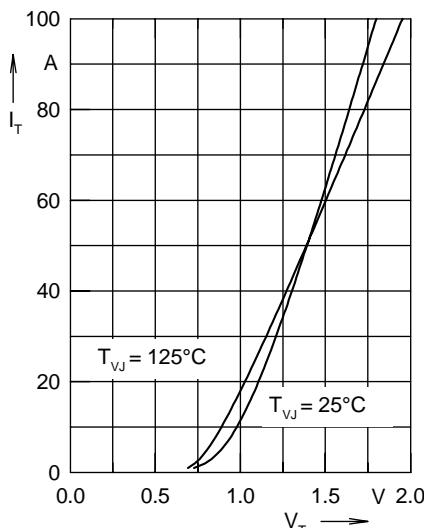


Fig. 3 Forward characteristics

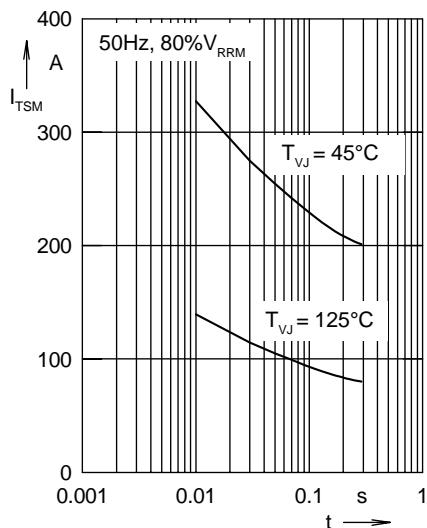


Fig. 4 Surge overload current
 I_{TSM} : crest value, t : duration

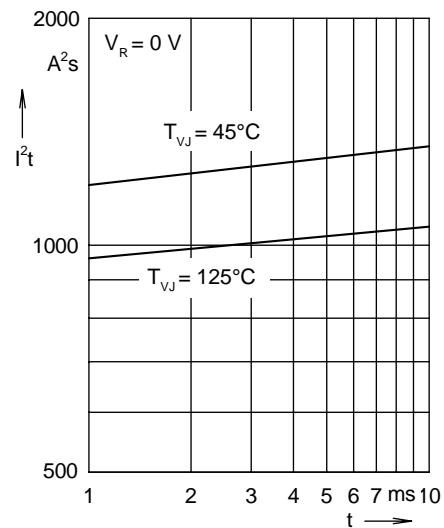


Fig. 5 I^2t versus time (1-10 ms)

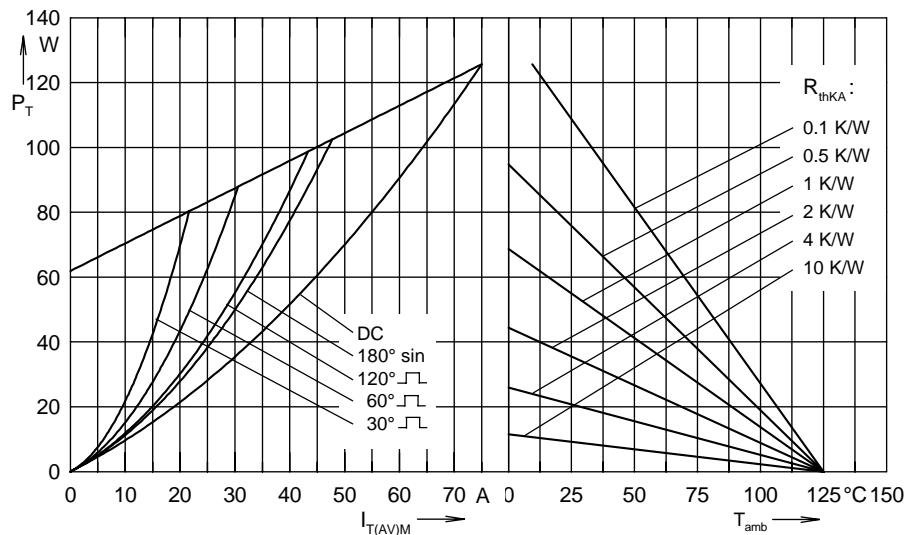


Fig. 6 Power dissipation versus forward current and ambient temperature

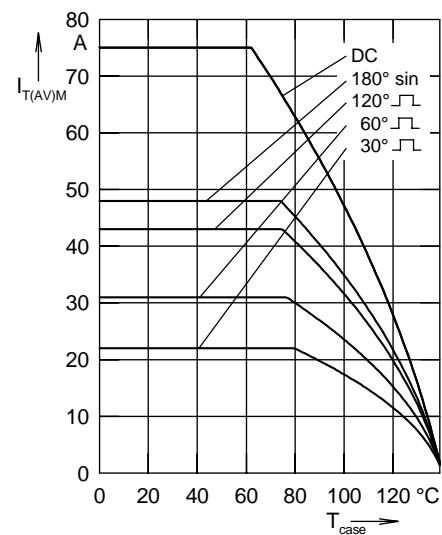


Fig. 7 Max. forward current at case temperature

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.62
180°	0.71
120°	0.748
60°	0.793
30°	0.817

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.206	0.013
2	0.362	0.118
3	0.052	1.488

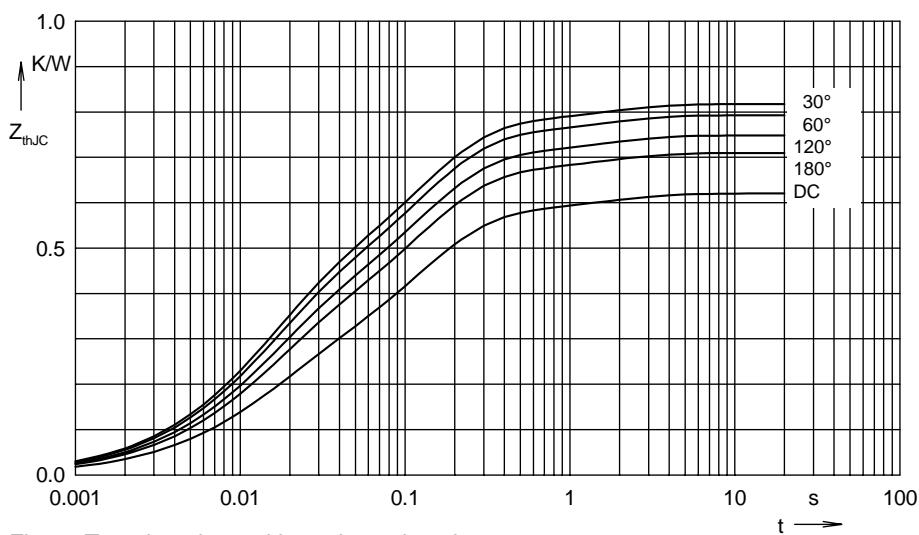


Fig. 8 Transient thermal impedance junction to case

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